

Improvement of thin-film transistor performance in atomic layer deposited SnO film by thermal annealing process

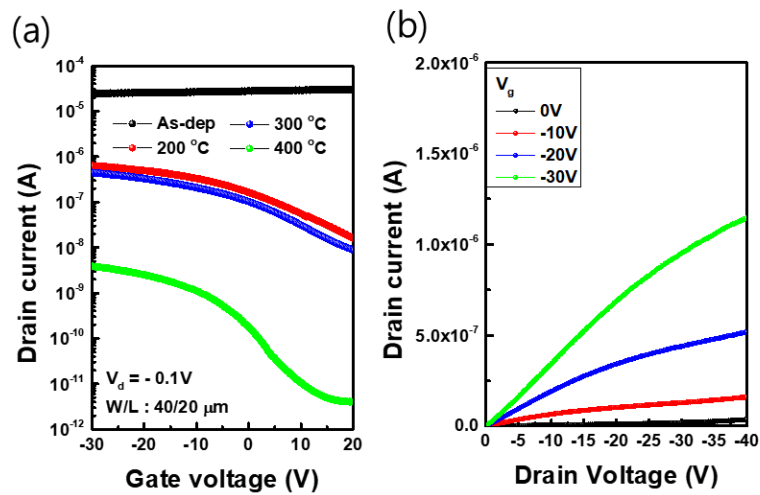


Figure 1. Transfer characteristic with drain voltage of -0.1 V (a), and output curve (b) of SnO TFTs